

MOTOROLA SEMICONDUCTOR TECHNICAL DATA

**The RF Line
SSB Power Transistors**

... designed primarily for wideband, large-signal output and driver amplifier stages in the 2 to 30 MHz frequency range.

- Designed for Class A, AB or C Power Amplifiers
- Specified 13.5 Volt, 28 MHz Characteristics:
 - Output Power — 75 Watts PEP
 - Power Gain — 15 dB Min, Class AB
- 100% Tested for Load Mismatch at All Phase Angles with $\infty:1$ VSWR
- Gold Metallization for Improved Reliability
- Diffused Ballast Resistors

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4	Vdc
Collector Current — Continuous	I_C	15	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	175 0.572	Watts $W/^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.75	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Base Breakdown Voltage ($I_C = 100\text{ mA}$, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 6\text{ mA}$, $I_C = 0$)	$V_{(BR)EBO}$	4	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 13.5\text{ V}$, $V_{BE} = 0$)	I_{CES}	—	—	10	mAdc

ON CHARACTERISTICS

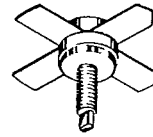
DC Current Gain ($I_C = 1\text{ A}$, $V_{CE} = 5\text{ V}$)	h_{FE}	25	—	150	—
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FUNCTIONAL TESTS

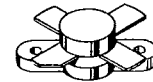
Common-Emitter Amplifier Power Gain ($V_{CE} = 13.5\text{ V}$, $P_{out} = 75\text{ W PEP}$, $f = 28\text{ MHz}$)	GPE	15	—	—	dB
Load Mismatch ($V_{CE} = 13.5\text{ V}$, $P_{out} = 75\text{ W PEP}$, $f = 28\text{ MHz}$, Load VSWR = $\infty:1$, All Phase Angles)	ψ	No Degradation in Output Power			
Intermodulation Distortion ($V_{CE} = 13.5\text{ Vdc}$, $P_{out} = 75\text{ W PEP}$, $f = 28\text{ MHz}$)	IMD	—	-32	—	dB

**PT9784
PT9784A**

15 dB
2-30 MHz
75 WATTS PEP
13.5 VOLTS
SSB POWER
TRANSISTORS



.380 SOE
CASE 145D-01, STYLE 1
PT9784A



.380 SOE F
CASE 211-07, STYLE 1
PT9784

TYPICAL CHARACTERISTICS

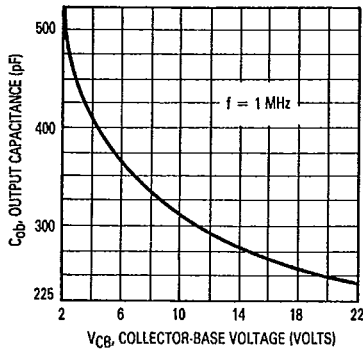


Figure 1. Output Capacitance versus Voltage

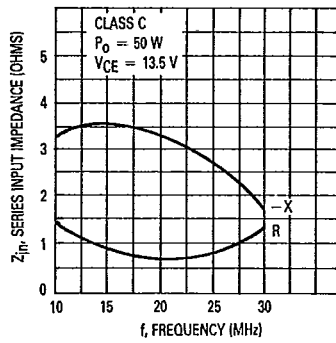


Figure 2. Series Input Impedance versus Frequency

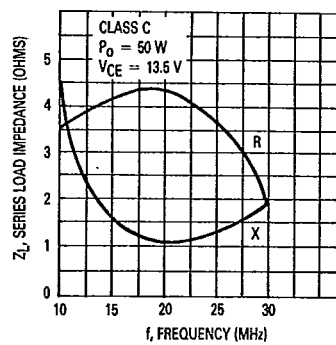
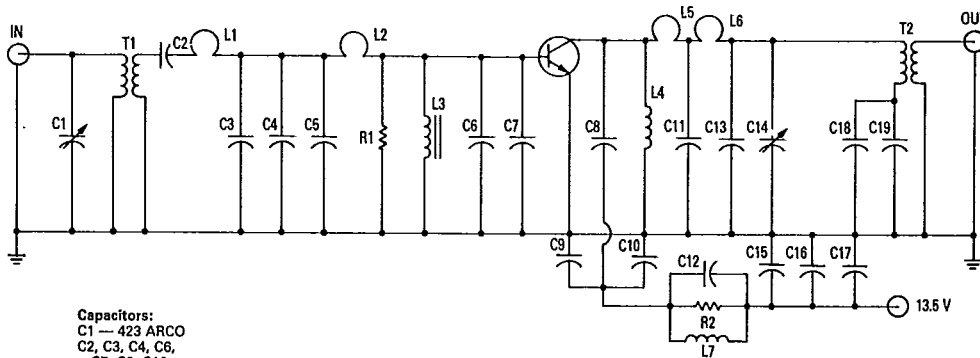


Figure 3. Series Load Impedance versus Frequency



- Capacitors:**
 C1 — 423 ARCO
 C2, C3, C4, C6, C7, C9, C10, C13, C18, C19 — 1000 pF UNELCO
 C5 — 500 pF UNELCO
 C8 — 400 pF UNELCO
 C11 — 250 pF UNELCO
 C12, C15 — 0.1 Disc.
 C14 — 469 ARCO
 C16 — 0.01 Disc.
 C17 — 25 MFD, 35 Volts
- Resistors:**
 R1 — 51 Ohms
 R2 — 16 Ohms 2 W
- Colls:**
 L1 — #18 AWG, 1-3/8" Long, Looped 3/8" Curve
 L2 — #18 AWG, 1-1/8" Long, Looped 1/4" Curve
 L3 — 2-1/2 T, #24 AWG, Looped thru Ferroxcube VK21107-3B
 L4 — 8 T, #18 AWG, 2 ID, 5-8" Long
 L5 — #18 AWG, 1/4" Long, straight
 L6 — #18 AWG, 1/2" Long, Looped 3/8" Curve
 L7 — 10 T, #20 AWG, Enamel, Wrapped around 16 Ohm, 2 Watt resistor
- Transformers:**
 T1 — Primary — 4 T, #22 AWG, Teflon insulated
 Secondary — Brass Tube, Length — 11/16"
 T2 — Primary — Brass Tube, Secondary — 3 T, #22 AWG
 Teflon insulated, Length — 1-1/4"

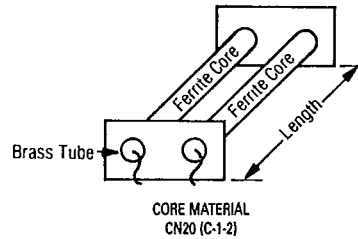


Figure 4. 28 MHz Test Circuit